

InGaAs-APD/Preamp_____ **FRM5W231KT/LT** **Receiver**

FEATURES

- Data rate up to 2.5Gb/s
- -32dBm typ. sensitivity
- 30 μ m active area APD chip with GaAs pre-amplifier
- Small co-axial package with single mode fiber

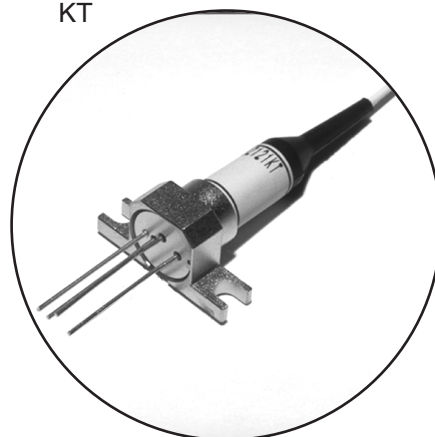
APPLICATIONS

- High bit rate long haul optical transmission systems operating at 2.5Gb/s

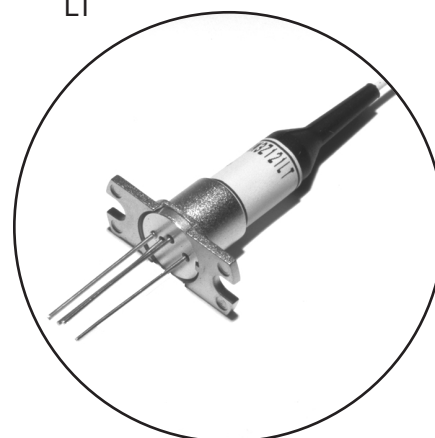
DESCRIPTION

These APD preamplifiers use an InGaAs APD chip with GaAs IC preamplifier. The KT package is designed for a horizontal PC board mount. The LT package is secured by a vertical flange. Each package is connected with single mode fiber by Nd: YAG welding. The detector preamplifier is DC coupled and has a low electrical output when the APD is illuminated.

KT



LT



ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Storage Temperature	T_{stg}	-40 to +85	$^\circ\text{C}$
Operating Temperature	T_{op}	-40 to +85	$^\circ\text{C}$
Supply Voltage	V_{SS}	-7 to 0	V
APD Reverse Voltage	V_R (Note 1)	0 to V_B	V
APD Reverse Current	I_R (Note 2)	0.6	mA

OPTICAL & ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, $\lambda=1,310/1,550\text{nm}$, $V_{\text{SS}}=-5.2\text{V}$, unless otherwise specified)

Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
APD Responsivity	R15	1,550nm, M=1	0.80	0.85	-	A/W
	R13	1,310nm, M=1	0.75	0.85	-	A/W
APD Breakdown Voltage	V_B	$I_D=10\mu\text{A}$	40	50	65	V
Temperature Coefficient of V_B	γ	Note 3	0.08	0.12	0.15	$\text{V}/^\circ\text{C}$
AC Transimpedance	Z_t	AC-Coupled, $f=100\text{MHz}$, $R_L=50\Omega$, $\text{Pin} < -20\text{dBm}$,	400	600	-	Ω
Bandwidth	BW	AC-Coupled, $R_L=50\Omega$, $M=3$ to 15, -3dBm from 1MHz	1.8	2.0	-	GHz
Equivalent Input Noise Current Density	i_n	AC-Coupled, $R_L=50\Omega$, Average within BW	-	6.5	8	$\text{pA}/\sqrt{\text{Hz}}$
Sensitivity	P_r	2.488Gb/s NRZ, PRBS= $2^{23}-1$, B.E.R.= 10^{-10} , V_R is set at optimum value	-	-32	-31	dBm
		$T_C=-40$ to $+85^\circ\text{C}$	-	-31	-30	dBm
Maximum Overload	P_o	2.488Gb/s NRZ, M=3, PRBS= $2^{23}-1$, B.E.R.= 10^{-10} , V_R is set at optimum value	-5	-	-	dBm
		$T_C=-40$ to $+85^\circ\text{C}$, M=3	-7	-	-	dBm
Power Supply Current	I_{SS}	-	-	-	40	mA
Power Supply Voltage	V_{SS}	-	-5.46	-5.2	-4.94	V

Note: (1) V_B differs from device to device. V_B data is attached to each device.

(2) CW condition

(3) $\gamma=dV_B/dT_C$

Fig. 1 Output Characteristics

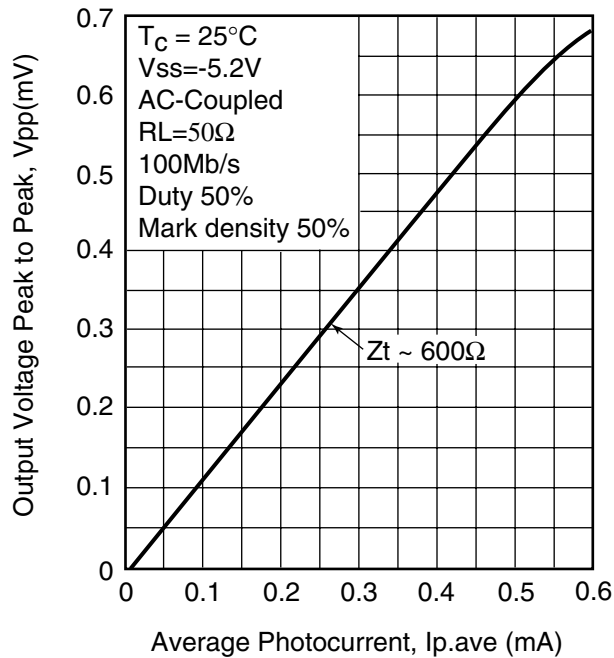


Fig. 2 Relative Frequency Response

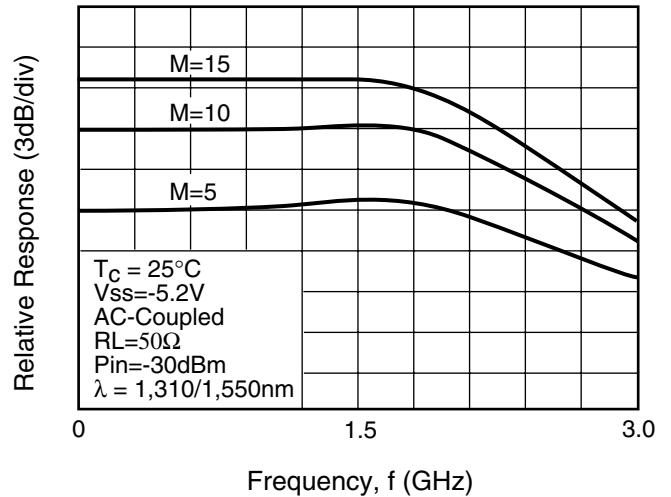
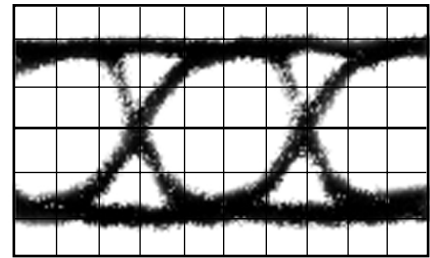
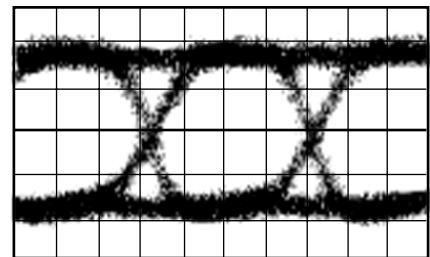


Fig.4 Eye Diagram with a 1,550nm, 2.5Gb/s NRZ, $2^{23}-1$ PRBS incident signal

Input optical wave form with Bessel filter



Equivalent output wave form at $P_{in} = -32\text{dBm}$, $T_c = 25^\circ\text{C}$, $M = \text{optimum}$



100ps/div

Fig.3 Equivalent Input Noise Current Density

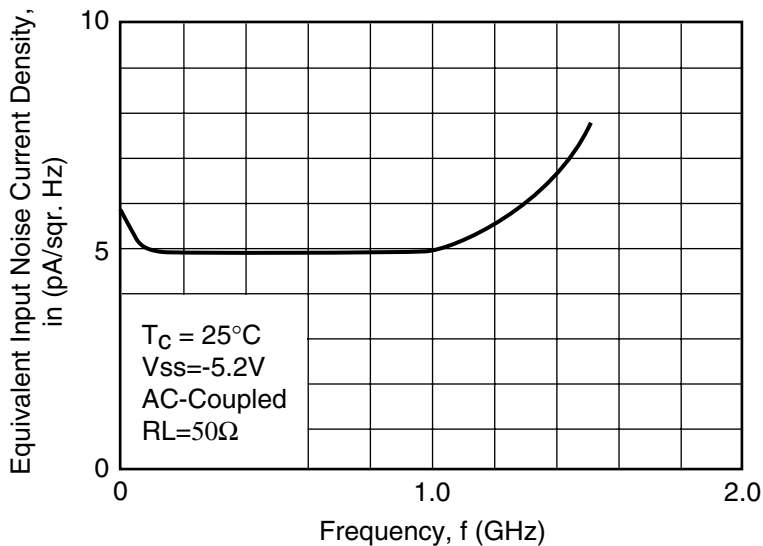
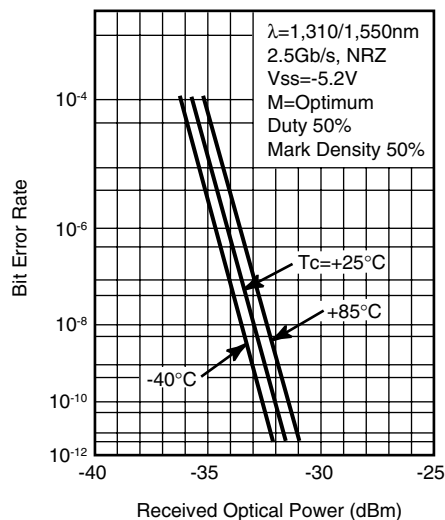
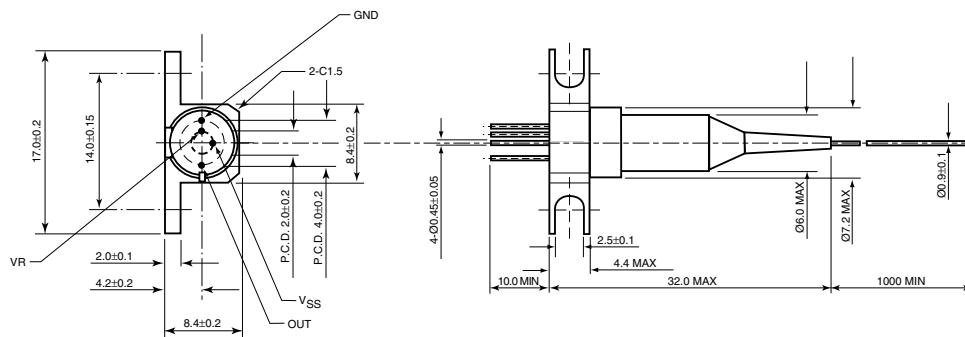


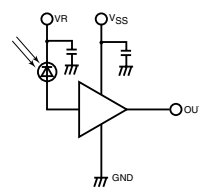
Fig.5 Bit Error Rate



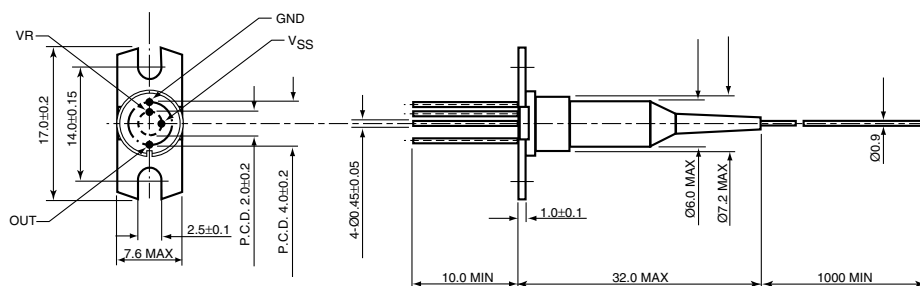
“KT” PACKAGE



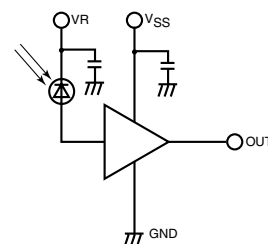
UNIT: mm



“LT” PACKAGE



UNIT: mm



InGaAs-APD/Preamp Receiver *FRM5W231KT/LT*

For further information please contact:

FUJITSU COMPOUND SEMICONDUCTOR, INC. Americas & R.O.W.

2355 Zanker Rd.
San Jose, CA 95131-1138, U.S.A.
Phone: (408) 232-9500
FAX: (408) 428-9111
www.fcsi.fujitsu.com

FME, QDD

Fujitsu Microelectronics Europe GmbH
Quantum Devices Division
Network House
Norreys Drive
Maidenhead, Berkshire SL6 4FJ
United Kingdom
TEL: +44 (0) 1628 504800
FAX: +44 (0) 1628 504888

FUJITSU QUANTUM DEVICES SINGAPORE PTE LTD.

Hong Kong Branch

Rm. 1101, Ocean Centre, 5 Canton Rd. Tsim Sha Tsui,
Kowloon, Hong Kong
TEL: +852-23770226
FAX: +852-23763269

FUJITSU QUANTUM DEVICES LIMITED

Global Business Division
Global Sales Support Department
Shinjuku Daiichiseimei Building, 2-7-1 Nishishinjuku,
Shinjuku-ku, Tokyo, 163-0721, Japan
TEL: +81-3-5322-3356
FAX: +81-3-5322-3398

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